

October 2013

# FQP9P25

# P-Channel QFET® MOSFET -250 V, -9.4 A, 620 mΩ

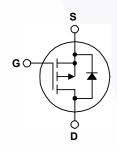
# **Description**

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

## **Features**

- -9.4 A, -250 V,  $R_{DS(on)} = 0.62 \Omega \text{ (Max.)}@V_{GS} = -10 \text{ V},$   $I_D = -4.7 \text{ A}$
- Low gate charge (typ. 29 nC)
- Low Crss (typ. 27 pF)
- 100% avalanche tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

g °					
Symbol	Parameter		FQP9P25	Unit	
$V_{DSS}$	Drain-Source Voltage		-250	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	-9.4	Α	
	- Continuous (T <sub>C</sub> = 100	°C)	-5.9	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-37.6	А	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	650	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	-9.4	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	12	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		120	W	
	- Derate above 25°C		0.96	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

# **Thermal Characteristics**

Symbol	Parameter	FQP9P25	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.04	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

# **Package Marking and Ordering Information**

Device Marking	Device	Package Reel Size		Tape Width	Quantity	
FQP9P25	FQP9P25	TO220	-	-	50	

# Flactrical Characteristics

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-250			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		-0.2		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -250 V, V <sub>GS</sub> = 0 V			-1	μА
		V <sub>DS</sub> = -200 V, T <sub>C</sub> = 125°C			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -4.7 A		0.48	0.62	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -40 V, I <sub>D</sub> = -4.7 A		5.7		S
<b>Dynam</b> C <sub>iss</sub>	ic Characteristics Input Capacitance			910	1180	pF
Coss	Output Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		170	220	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		27	35	pF
9155	Neverse Transier Supusitance				00	Pi
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -125 V, I <sub>D</sub> = -9.4 A,		20	50	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		150	310	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	3		45	100	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	65	140	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = -200 \text{ V}, I_{D} = -9.4 \text{ A},$		29	38	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = -10 V		7.6		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		14		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-9.4	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-37.6	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -9.4 A			-5.0	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = -9.4 \text{ A},$		190		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> / dt = 100 A/μs		1.45		μС

**Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 11.8mH, I $_{AG}$  = -9.4A, V $_{DD}$  = -50V, R $_{G}$  = 25  $\Omega$ , Starting T $_{J}$  = 25°C 3. I $_{SD}$  ≤ -9.4A, di/dt ≤ 300A/µs, V $_{DD}$  ≤ BV $_{DSS}$ , Starting T $_{J}$  = 25°C 4. Essentially independent of operating temperature

# **Typical Characteristics**

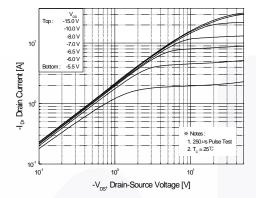


Figure 1. On-Region Characteristics

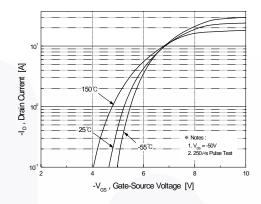


Figure 2. Transfer Characteristics

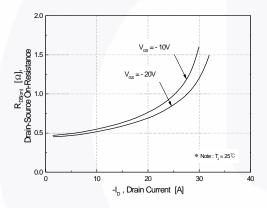


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

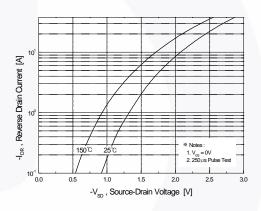


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

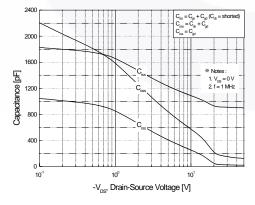


Figure 5. Capacitance Characteristics

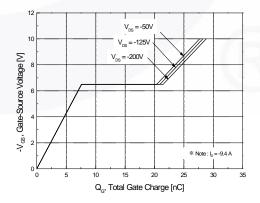


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

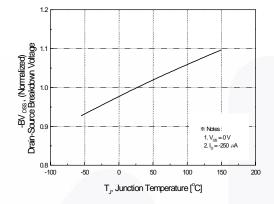


Figure 7. Breakdown Voltage Variation vs. Temperature

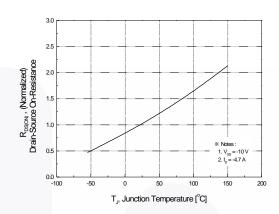


Figure 8. On-Resistance Variation vs. Temperature

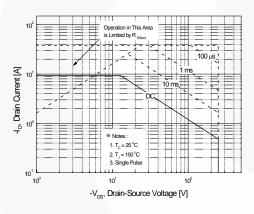


Figure 9. Maximum Safe Operating Area

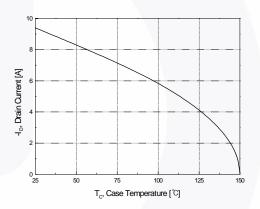


Figure 10. Maximum Drain Current vs. Case Temperature

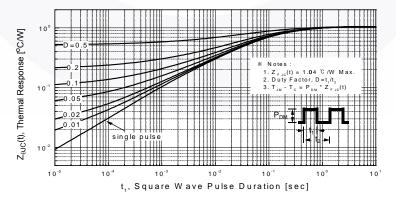


Figure 11. Transient Thermal Response Curve



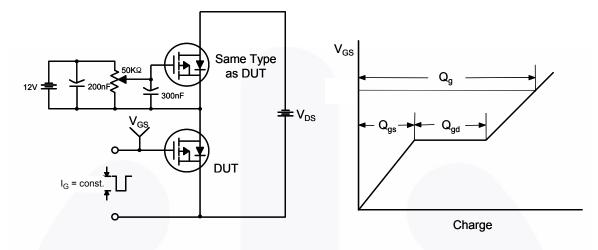


Figure 13. Resistive Switching Test Circuit & Waveforms

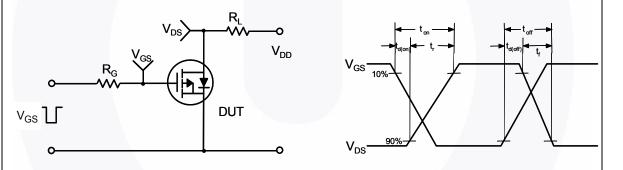


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

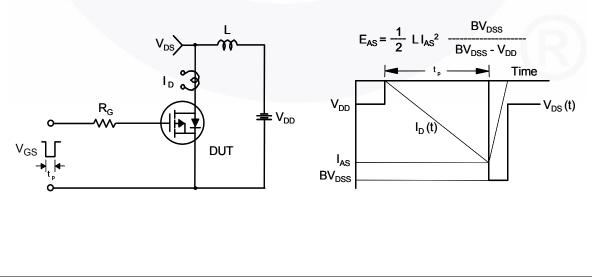


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms DUT I<sub>SD</sub> o Driver Compliment of DUT ‡ VDD (N-Channel)  $\prod V_{GS}$ • dv/dt controlled by R<sub>G</sub>  $\bullet$  I<sub>SD</sub> controlled by pulse period Gate Pulse Width  $V_{GS}$ Gate Pulse Period 10V (Driver) **Body Diode Reverse Current** I<sub>SD</sub> (DUT) di/dt  $I_{\text{FM}}$  , Body Diode Forward Current  $V_{DS}$  $V_{SD}$ (DUT) Body Diode Forward Voltage Drop Body Diode Recovery dv/dt

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# **Mechanical Dimensions**

# TO-220 3L

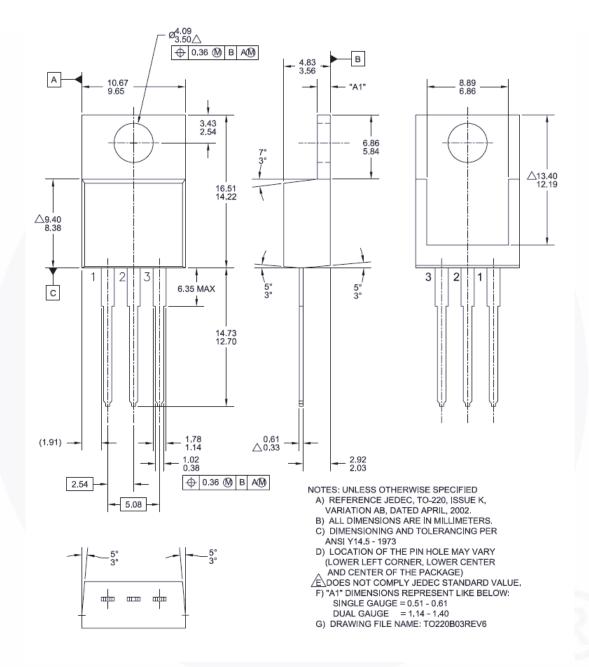


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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Dimension in Millimeters





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# > Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

# > Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

# Customer Service :

Email service@ameya360.com

# Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com